### Group IV Photonics Platforms for Sensing Applications

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**Abstract**— The mid-infrared (MIR) wavelength region has attracted interest due to a host of important application areas, such as sensing, medical diagnostics, industrial control, communications, defence and security [1,2]. Of particular importance is the so-called 'fingerprint' region where high selectivity sensing can be achieved. Integrated, compact, low cost and low energy solutions in group IV materials will have significant advantages over expensive and bulky spectrometers currently used.

Due to absorption properties of photonic materials [3], variety of potential applications and several fabrication issues in the MIR, different material platforms need to be considered for this wavelength range. In the last 3 years, MIR devices in SOI [4,5], SOS [6], Si on porous Si (SiPSi) [7], and Geon-Si [8] have been reported. SOI platform is probably the most desirable, as it has been extensively used for telecommunication wavelengths and fabrication recipes and designed rules are mature and can be readily transferred to the MIR. We have investigated this platform up to 4 µm and showed that the propagation loss can as low as 3 dB/cm for 400 nm thick SOI waveguides and at the wavelength of 3.8 µm. We have also demonstrated passive components based on this structure, including multimode interference (MMI) splitters, ring resonators, Mach-Zehnder interferometers (MZIs) [4], and spectrometers [9].

In order to extend the operational wavelength range even further, we have examined suspended structures in which the buried oxide layer has been removed [5]. Our simulations show that this structure can be used up to  $6.5\,\mu m$  for the Si overlayer thickness of  $500\,n m$  [10]. For the fingerprint region, the most promising candidate is Ge, and different Ge-based platforms can be considered.

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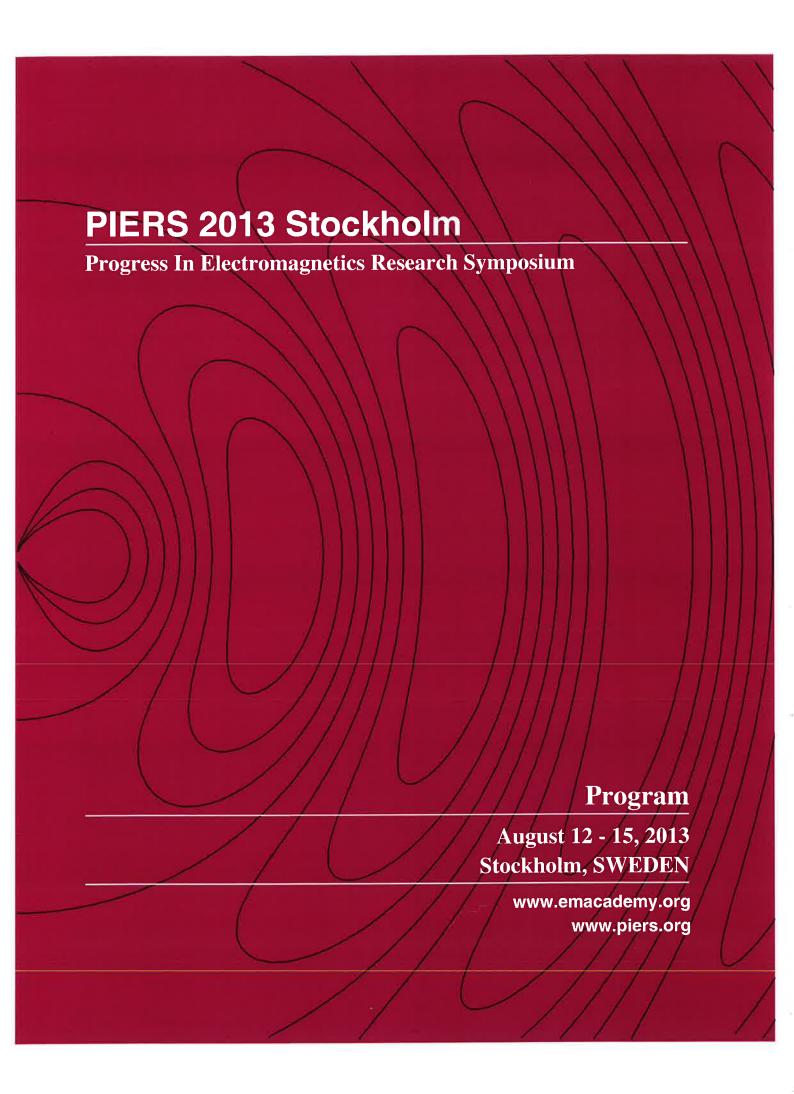
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## Session 3A9a SC3: On-chip Optical Sensing Technologies and Devices

Silicon Nanophotonics On-chip Sensing	
Peter Bienstman, Sam Werquin, Cristina Lerma Arce, Elewout Hallynck, Tom Claes, Jan-	
Willem Hoste, Daan Martens,	103
SiC Based pH Sensor with Gd <sub>2</sub> O <sub>3</sub> /Si <sub>3</sub> N <sub>4</sub> Gate Dielectrics	
D. H. Ko, C. S. Huang, Liann-Bie Chang, Jer-Ming Jeng, C. S. Lai, Y. T. Lin, Chow Lee,	1033
Optical Sensing and Particle Manipulation Using Silicon-based Microresonators in Optofluidic Chips	
Andrew Wing On Poon, Ting Lei, Jiawei Wang,	103
Directional Plasmonic Nanoantennas for Spectroscopy and Sensing	
Timur Shegai, Vladimir D. Miljkovic, P. Johansson, Mikael Kall,	1038
Group IV Photonics Platforms for Sensing Applications	
Goran Z. Mashanovich, M. Nedeljkovic, X. Chen, J. Soler Penades, G. Madalinski, M. Muneeb,	
Gunther Roelkens, H. M. H. Chong, G. T. Reed,	103'
New Fabrication and Instrumentation Techniques for Nanoplasmonic Biosensors	
Sang-Hyun Oh,	1038
Detection of Environmental Contaminants Using an Optical Refractometer and Silicon-on-Insulator (SOI)	
Devices	
John E. Saunders, Weijian Chen, Chris Brauer, Jack A. Barnes, Scott SH. Yam, Dan-Xia Xu,	
Hans-Peter Loock.	1039





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